

ABSTRACT

A throughput during a process of forming a thin film is improved and a thin film of high quality is produced at low cost.

5 For this purpose, a film forming system comprises a chamber 8, a precursory gas supplying line 2 to supply the chamber 8 with precursory gas, a reactive gas supplying line 1 to supply the chamber 8 with reactive gas, and a purge gas supplying line 3 to supply purge gas that purges the
10 precursory gas and the reactive gas, and forms a thin film on a substrate 82 in the chamber 8 by supplying the precursory gas or the reactive gas and purging alternately, and further comprises a middle line 22 having a certain volume that is arranged on a part or all of the precursor
15 supplying line 2 and into which the precursory gas can be filled at a time when the precursory gas is not supplied, and/or a middle line 12 having a certain volume that is arranged on a part or all of the reactive gas supplying line 1 and into which the reactive gas can be filled at a time
20 when the reactive gas is not supplied.